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Advanced Photonix, Inc. PDG-V455-46

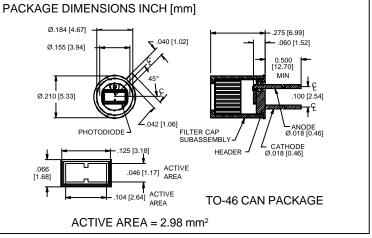
For any questions, you can email us directly: <u>sales@integrated-circuit.com</u>



Distributor of Advanced Photonix, Inc. : Excellent Integrated System Limited Datasheet of PDG-V455-46 - PHOTODIODE 550NM 2.98MM SQ TO-46 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

PHOTONIC Silicon Photodiode, Filter Combination Photovoltaic DETECTORS INC. (center wavelength 550 nm) Type PDG-V455-46





DESCRIPTION

The **PDG-V455-46** is a silicon, PIN planar diffused, photodiode with a narrow band interferance filter. The detector filter combination has a narrow 10 nm half bandwidth designed for low noise photovoltaic applica-

APPLICATIONS

- Spectrophotometry
- Chemistry instrumentation
- Liquid chromatography

tions. Packaged in a TO-46 metal can. ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	Ĩ				
Vbr	Reverse Voltage		75	V	₹				
T _{stg}	Storage Temperature	-20	+85	°C					
To	Operating Temperature Range	-15	+70	°C	NSN0				
Ts	Soldering Temperature*		+240	°C	SPC				
I L	Light Current		0.5	mA	Ű.				

SPECTRAL RESPONSE

0.7										
0.6		-		-						
0.5			<u>,0</u> 6	0	K					
0.4	-	¥.		r	-					
0.3		\vdash		\vdash	⊢					
0.2	<u> </u>									
0.1		-	-	┢	-	FW	HM	= 1	0 n	in –
0				Ш		Q	00 /	Tx	MI	N
100	0.00	200	400	000	600	001	0.00	900		100

WAVELENGTH (nm)

*1/16 inch from case for 3 secs max

FEATURES

• 550 nm CWL

• 10 nm FWHM

Large active area

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
lsc	Short Circuit Current***	H = 100 fc, 2850 K	35	40		μA
ΙD	Dark Current	H = 0, V _R = 10 V		150	300	pА
Rsн	Shunt Resistance	H = 0, V _R = 10 mV	1.0	6		GΩ
TC Rsh	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
CJ	Junction Capacitance	H = 0, V _R = 0 V**		340		pF
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		550		nm
HBW	Half Bandwidth	(FWHM)		10		nm
Vbr	Breakdown Voltage	I = 10 µµA	30	50		V
N EP	Noise Equivalent Power	V _R = 10 mV @ Peak		5x10 ⁻¹⁴		W/ V Hz
tr	Response Time	$RL = 1 K\Omega V_R = 0 V$		450		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f = 1 MHz, ***without filter [FORM NO. 100-PDG-V455-46 REV N/C]